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		FILING DATE	GROUP

(37 CFR 1.98(b))

U.S. PATENT DOCUMENTS

EXAM- INER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	0 0 5 5 6 6 0	5/9/2002	K. R. Lassila, et al.	568	616	10/11/2001
	5 9 4 8 4 6 4	9/7/1999	F. M. Delnick	427	77	6/19/1996
	5 9 7 7 0 4 1	11/2/1999	K. Honda	510	175	9/23/1997
	6 1 5 2 1 4 8	11/28/2000	A. M. George, et al.	134	2	9/3/1998
	6 3 1 3 1 8 2	11/6/2001	K. R. Lassila, et al.	516	204	5/4/1999
	0 1 1 5 0 2 2	8/22/2002	S. A. Messick, et al.	430	311	2/21/2001

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
EP	1 1 1 5 0 3 5		Europe			X	
JP 95	1 4 2 3 4 9		Japan			X	
JP 96	0 0 8 1 6 3		Japan			X	
WO 0	0 0 3 3 0 6		World			X	
WO 0	2 2 3 5 9 8		World			X	
WO 8	7 0 3 3 8 7		World			X	
WO 9	9 1 5 6 0 9		World			X	
WO 9	9 6 0 0 8 3		World			X	
WO 9	9 6 0 4 4 8		World			X	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Domke, W. D., et al., "Pattern Collapse in High Aspect Ratio DUV and 193nm Resists," Proc. SPIE-Int. Soc. Opt. Eng. 3999, 313-321, 2000.
	Cheung, C., et al., "A Study of a Single Closed Contact for 0.18 Micron Photolithography Process," Proc. SPIE-Int. Soc. Opt. Eng. 3998, 738-741, 2000.
	S. Hien, et al., "Collapse behavior of single layer 193 and 157 nm resists: Use of surfactants in the rinse to realize the sub 130 nm nodes," Infineon Technologies, International SEMATECH, Center for Nano Technology, University of Wisconsin.
	T. Tanaka, et al., "Mechanism of Resist Pattern Collapse During Development Process," Jpn. J. Appl. Phys. Vol. 32 (1993), pp. 6059-6064, Part 1, No. 12B.

EXAMINER	DATE CONSIDERED
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